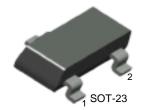


KST17

CATV Transistor



1. Base 2. Emitter 3. Collector

NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings T_a =25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	20	V
V_{CEO}	Collector-Emitter Voltage	15	V
V _{EBO}	Emitter-Base Voltage	3.0	V
P _C	Collector Dissipation (T _a =25°C)	6.25	mA
	Derate above 25°C	5.0	mA/°C
TJ	Junction Temperature	150	mW
T _{STG}	Storage Temperature	-55 ~ 150	°C
R _{TH} (j-a)	Thermal Resistance junction to Ambient	200	°C/W

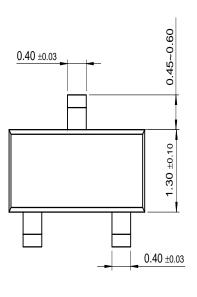
Refer to KSP17 for graphs

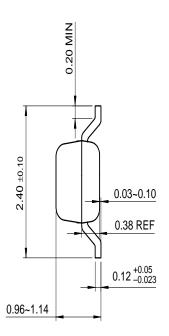
$\textbf{Electrical Characteristics} \ \, \textbf{T}_{a} \!\!=\!\! 25^{\circ} \textbf{C} \ \, \text{unless otherwise noted}$

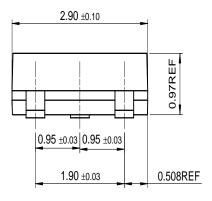
Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	I _C =100μA, I _E =0	20			V
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C =1mA, I _B =0	15			V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_{E}=10\mu A, I_{C}=0$	3.0			V
I _{CBO}	Collector Cut-off Current	V_{CB} =15V, I_{E} =0			100	nA
h _{FE}	DC Current Gain	V_{CE} =10V, I_{C} =5mA	25		250	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C =10mA, I _B =1mA			0.5	V
f _T	Current Gain Bandwidth Product	V _{CE} =10V, I _C =5mA, f=100MHz	800			MHz
C _{ob}	Output Capacitance	V_{CB} =10V, I_{E} =0, f =1MHz	0.3		0.9	pF
h _{fe}	Small Signal Current Gain	V _{CB} =10V, I _C =5mA, f=1MHz	30			
NF	Noise Figure	V_{CC} =12V, I_{C} =5mA R_{S} =50 Ω , f=200MHz			6.0	dB
G _{PE}	Power Gain	V_{CC} =12V, I_{C} =5mA R_{S} =50 Ω , f=200MHz		24		dB

Package Demensions

SOT-23







Dimensions in Millimeters

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